

Description

The DGTD65T15H2TF is produced using advanced Field Stop Trench IGBT Technology, which provides high performance, excellent quality and high ruggedness.

Features

- High Ruggedness for Motor Control
- $V_{CE(sat)}$ Positive Temperature Coefficient
- Very Soft, Fast Recovery Anti-Parallel Diode
- Low EMI
- Maximum Junction Temperature +175°C
- Lead-Free Finish & RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

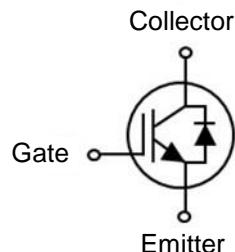
- Motor Controls

Mechanical Data

- Case: ITO220AB (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 1.9 grams (Approximate)



ITO220AB (Type MC)



Device Symbol

Ordering Information (Note 4)

Product	Marking	Quantity
DGTD65T15H2TF	DGTD65T15H2	1000 per Box in Tubes

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



○○○ = Manufacturer's Marking
 DGTD65T15H2 = Product Type Marking Code
 YY = Year (ex: 17 = 2017)
 WW = Week (01 to 53)

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CE}	650	V
DC Collector Current, Limited by T_{vjmax}	$T_C = +25^\circ\text{C}$	30	A
		15	A
Pulsed Collector Current, t_p Limited by T_{vjmax}	I_{Cpuls}	60	A
Diode Forward Current Limited by T_{vjmax}	$T_C = +25^\circ\text{C}$	30	A
		15	A
Diode Pulsed Current, t_p Limited by T_{vjmax}	I_{Fpuls}	60	A
Gate-Emitter Voltage	V_{GE}	± 20	V
Short Circuit Withstand Time $V_{CC} \leq 360\text{V}$, $V_{GE} = 15\text{V}$, $T_{vj} = +150^\circ\text{C}$	t_{SC}	5	μs

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	$T_C = +25^\circ\text{C}$	48	W
		24	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case for IGBT (Note 5)	$R_{\theta JC}$	3.0	
Thermal Resistance, Junction to Case for Diode (Note 5)	$R_{\theta JC}$	5.0	
Operating Temperature	T_{vj}	-40 to +175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Electrical Characteristics (@ $T_{vj} = +25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
STATIC CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BV_{CES}	650	—	—	V	$I_C = 2\text{mA}$, $V_{GE} = 0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	—	1.65	2.00	V	$I_C = 15\text{A}$, $V_{GE} = 15\text{V}$
$T_{vj} = +175^\circ\text{C}$		—	1.90	—		
Diode Forward Voltage	V_F	—	1.85	2.30	V	$V_{GE} = 0\text{V}$, $I_F = 15\text{A}$
$T_{vj} = +25^\circ\text{C}$		—	1.95	—		
Gate-Emitter Threshold Voltage	$V_{GE(\text{th})}$	4.5	5.5	6.5	V	$V_{CE} = V_{GE}$, $I_C = 0.5\text{mA}$
Zero Gate Voltage Collector Current	I_{CES}	—	—	20	μA	$V_{CE} = 650\text{V}$, $V_{GE} = 0\text{V}$, $T_{vj} = +25^\circ\text{C}$
Gate-Emitter Leakage Current	I_{GES}	—	—	± 100	nA	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$
DYNAMIC CHARACTERISTICS						
Total Gate Charge	Q_g	—	61	—	nC	$V_{CE} = 520\text{V}$, $I_C = 15\text{A}$, $V_{GE} = 15\text{V}$
Gate-Emitter Charge	Q_{ge}	—	11	—		
Gate-Collector Charge	Q_{gc}	—	35	—		
Input Capacitance	C_{ies}	—	1129	—	pF	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$
Reverse Transfer Capacitance	C_{res}	—	57	—		
Output Capacitance	C_{oes}	—	31	—		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(\text{on})}$	—	19	—	ns	$V_{GE} = 15\text{V}$, $V_{CC} = 400\text{V}$, $I_C = 15\text{A}$, $R_G = 10\Omega$, Inductive Load, $T_{vj} = +25^\circ\text{C}$
Rise Time	t_r	—	27	—		
Turn-Off Delay Time	$t_{d(\text{off})}$	—	128	—		
Fall Time	t_f	—	32	—		
Turn-On Switching Energy	E_{on}	—	270	—		
Turn-Off Switching Energy	E_{off}	—	86	—		
Total Switching Energy	E_{ts}	—	356	—	ns	$V_{GE} = 15\text{V}$, $V_{CC} = 400\text{V}$, $I_C = 15\text{A}$, $R_G = 10\Omega$, Inductive Load, $T_{vj} = +175^\circ\text{C}$
Turn-On Delay Time	$t_{d(\text{on})}$	—	17	—		
Rise Time	t_r	—	29	—		
Turn-Off Delay Time	$t_{d(\text{off})}$	—	150	—		
Fall Time	t_f	—	130	—		
Turn-On Switching Energy	E_{on}	—	342	—		
Turn-Off Switching Energy	E_{off}	—	288	—	ns	$I_F = 15\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$, $T_{vj} = +25^\circ\text{C}$
Total Switching Energy	E_{ts}	—	630	—		
Reverse Recovery Time	t_{rr}	—	150	—		
Reverse Recovery Current	I_{rr}	—	5.2	—	A	
Reverse Recovery Charge	Q_{rr}	—	390	—	nC	$I_F = 15\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$, $T_{vj} = +175^\circ\text{C}$
Reverse Recovery Time	t_{rr}	—	207	—	ns	
Reverse Recovery Current	I_{rr}	—	6.1	—	A	
Reverse Recovery Charge	Q_{rr}	—	631	—	nC	

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

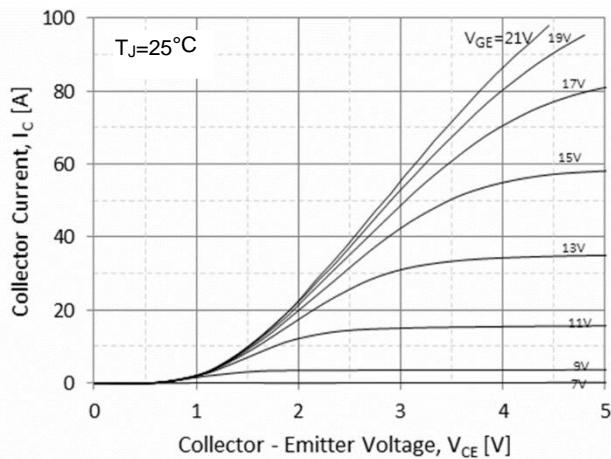


Fig.1 Typical Output Characteristics($T_j=25^\circ\text{C}$)

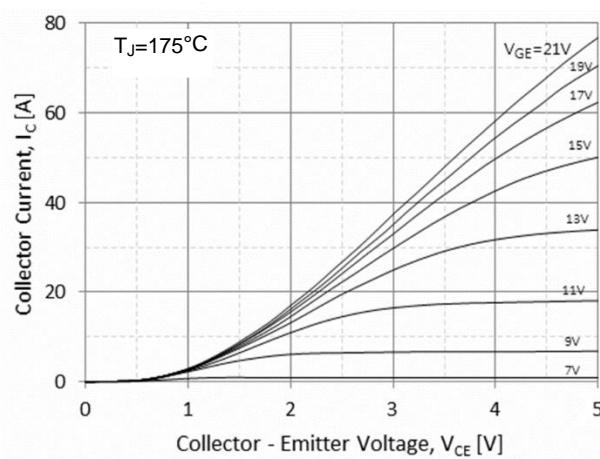


Fig.2 Typical Output Characteristics($T_j=175^\circ\text{C}$)

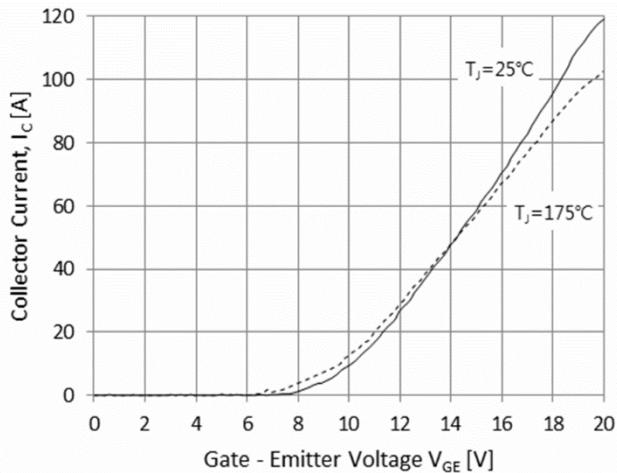


Fig.3 Typical Transfer Characteristics

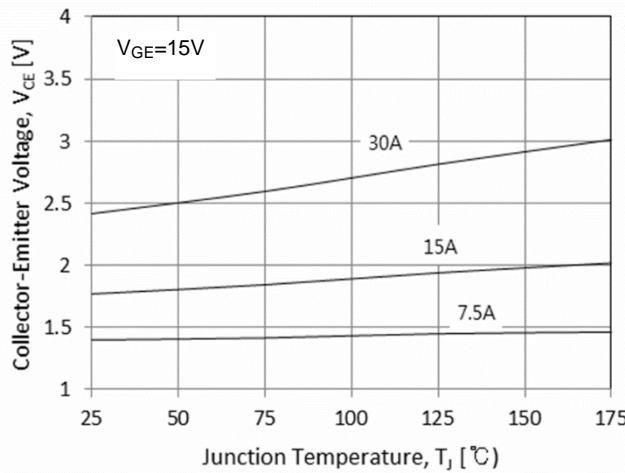


Fig.4 Typical Collector-Emitter Saturation Voltage - Junction Temperature

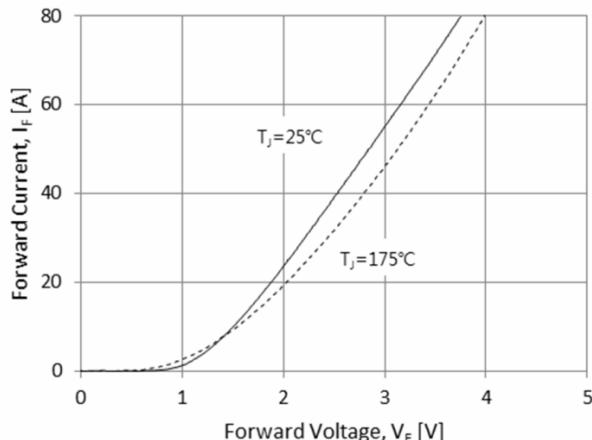


Fig.5 Diode Forward Characteristics

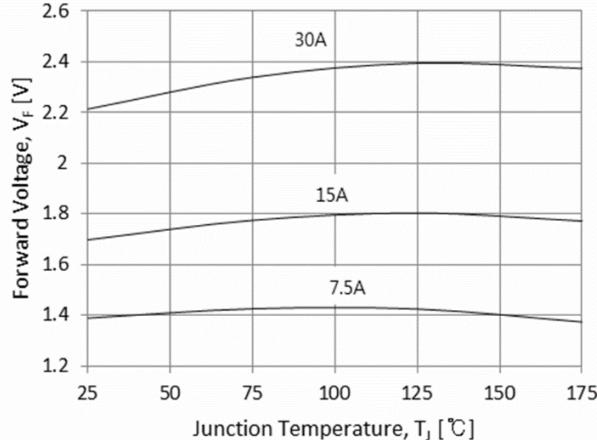


Fig.6 Diode Forward-Junction Temperature

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.) (Cont.)

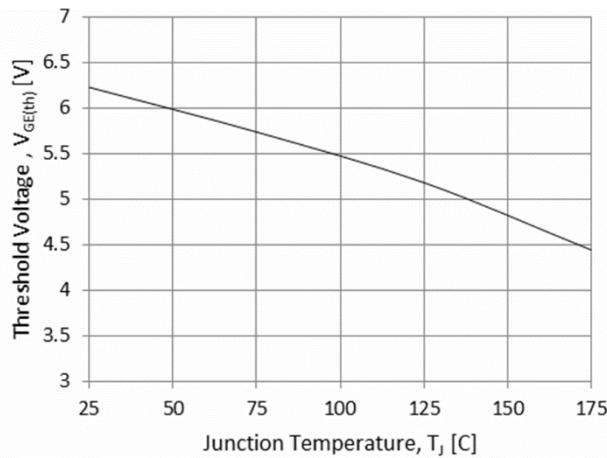


Fig.7 Threshold Voltage-Junction Temperature

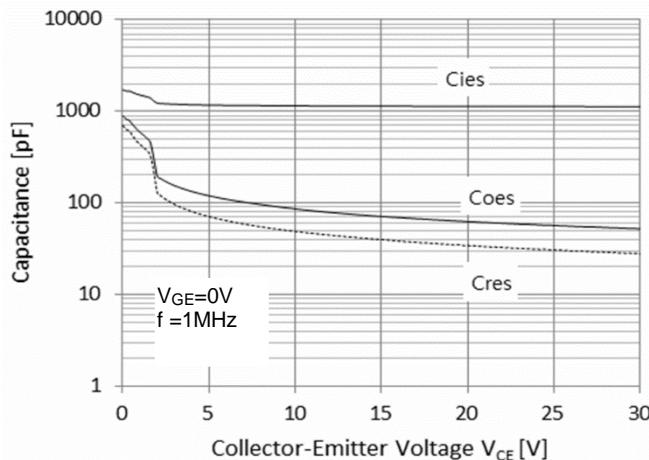


Fig.8 Typical Capacitance

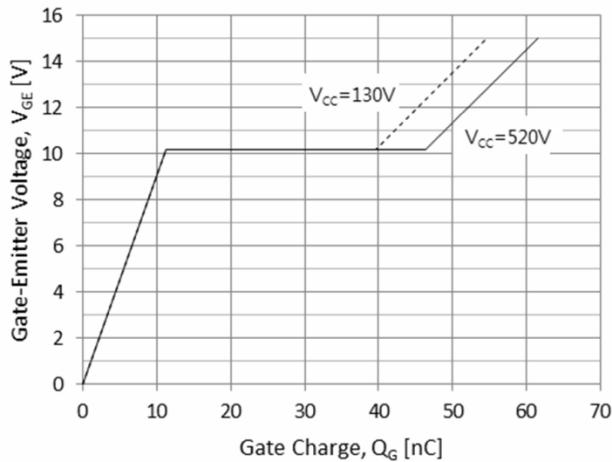


Fig.9 Typical Gate Charge

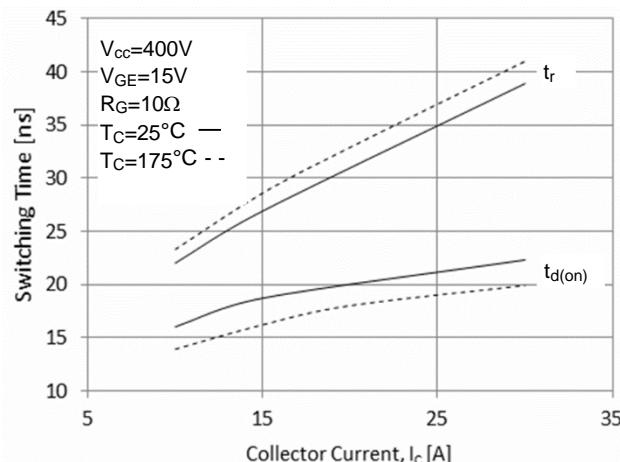


Fig.10 Typical Turn on-Collector Current

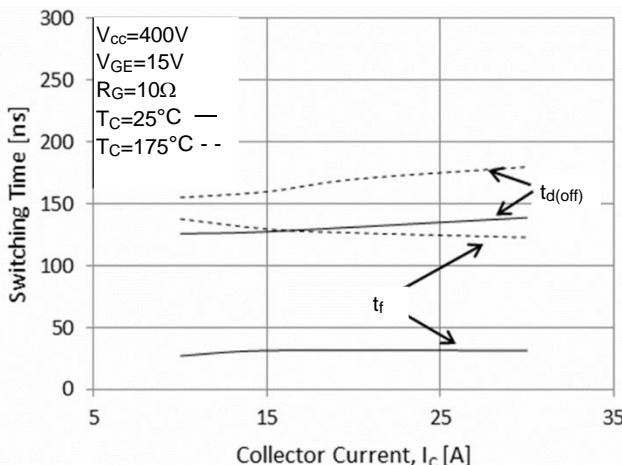


Fig.11 Typical Turn off-Collector Current

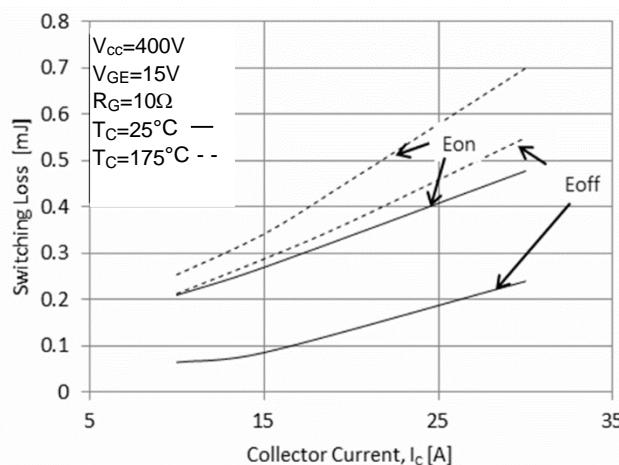


Fig.12 Switching Loss-Collector Current

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.) (Cont.)

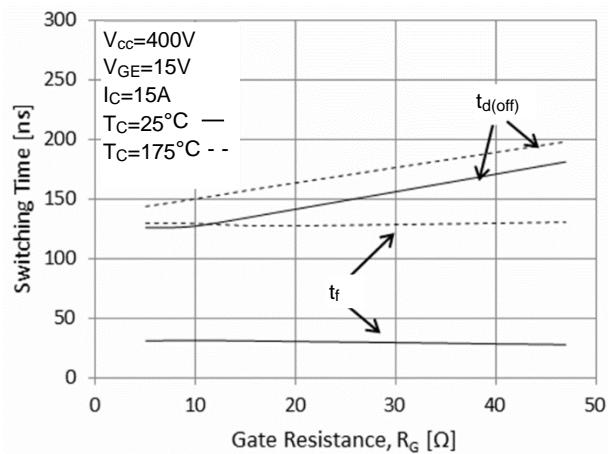
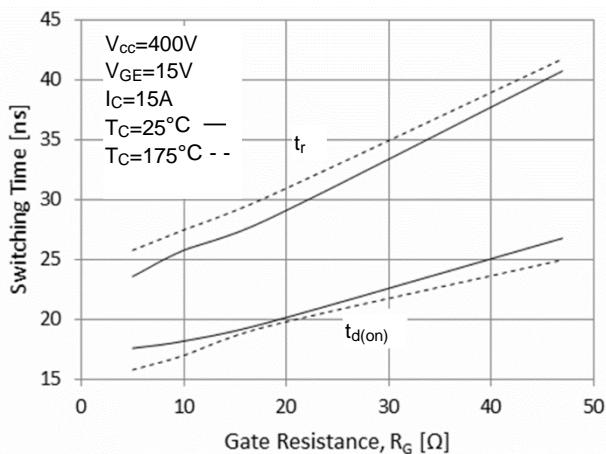


Fig.13 Turn on Characteristics-Gate Resistance

Fig.14 Turn off Characteristics-Gate Resistance

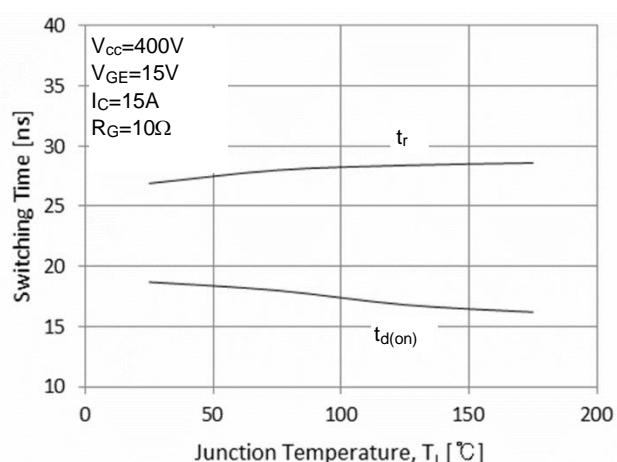
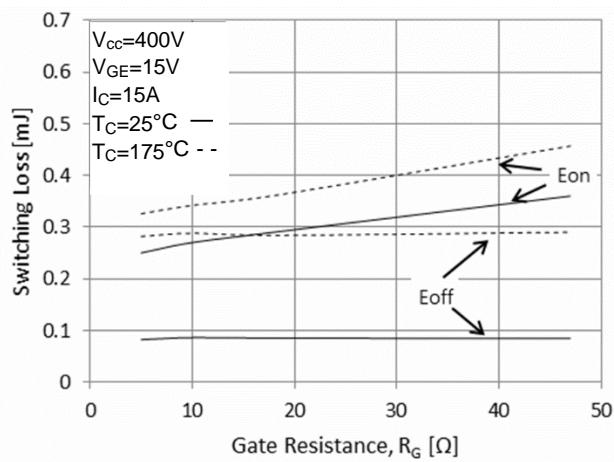
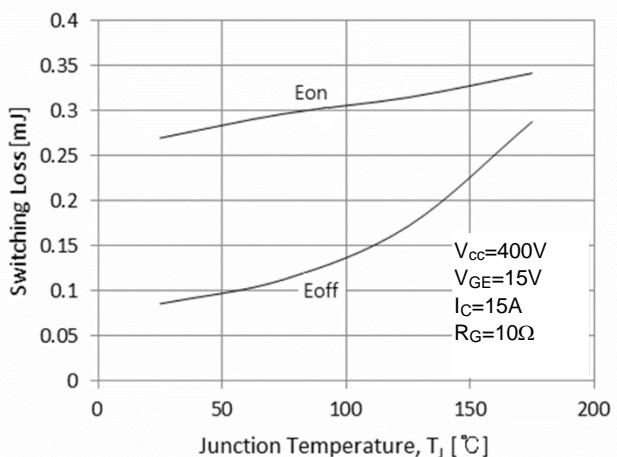
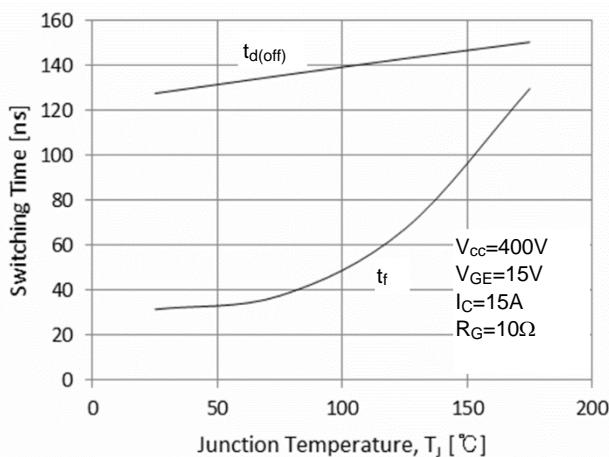


Fig.15 Switching Loss-Gate Resistance

Fig.16 Turn on Characteristics-Junction Temperature



Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.) (Cont.)

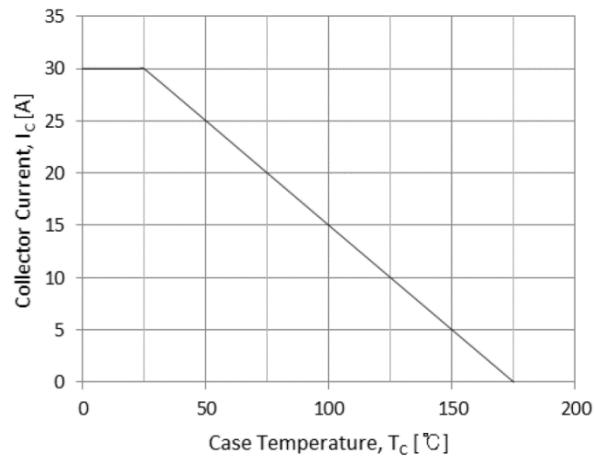
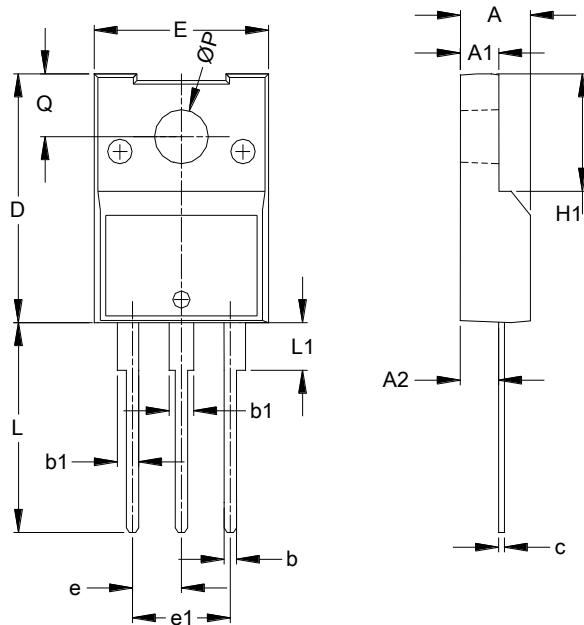


Fig.19 Case Temperature-Collector Current

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

ITO220AB (Type MC)



ITO220AB (Type MC)			
Dim	Min	Max	Typ
A	4.30	4.80	--
A1	2.50	3.10	--
A2	2.30	2.90	--
b	0.50	1.00	--
b1	0.95	1.70	--
c	0.40	0.80	--
D	14.50	16.40	--
H1	6.20	7.20	--
E	9.60	10.40	--
e	--	--	2.54
e1	--	--	5.08
L	12.20	14.20	--
L1	2.90	4.70	--
P	3.00	3.40	--
Q	2.40	3.50	--

All Dimensions in mm

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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